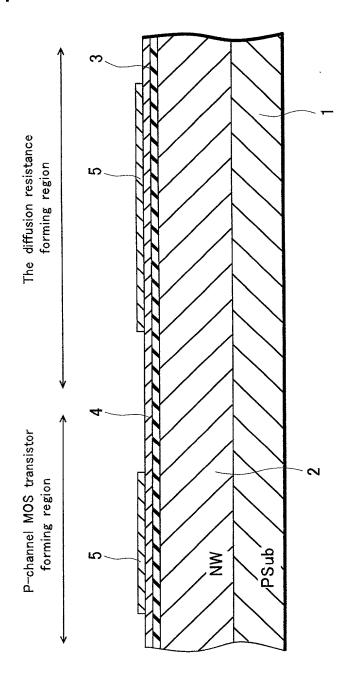
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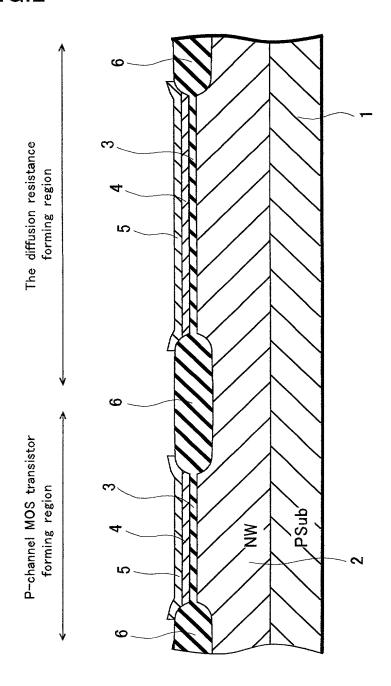
FIG.1



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FIG.2



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FIG.3

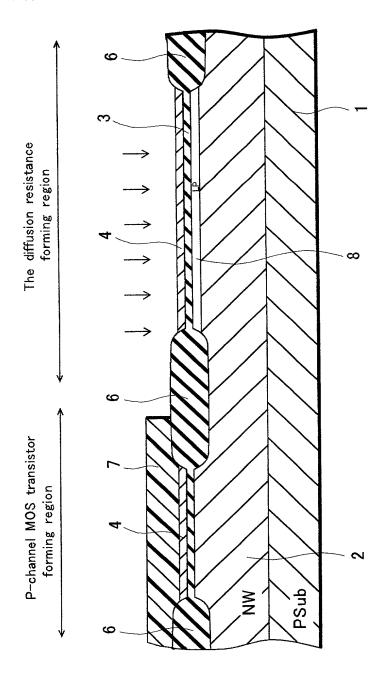
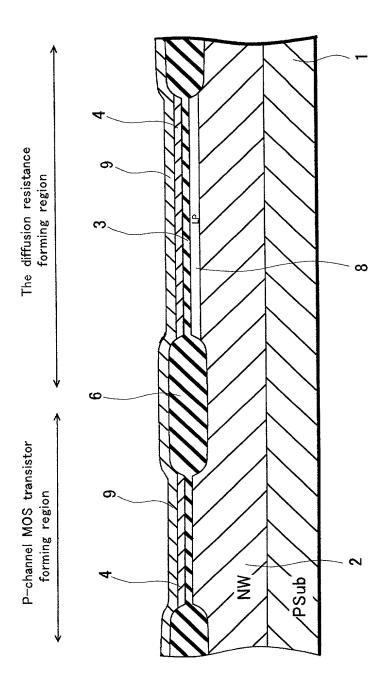


FIG.4



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FIG.5

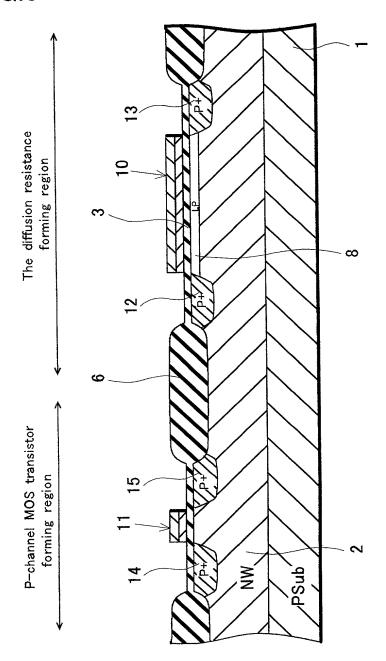
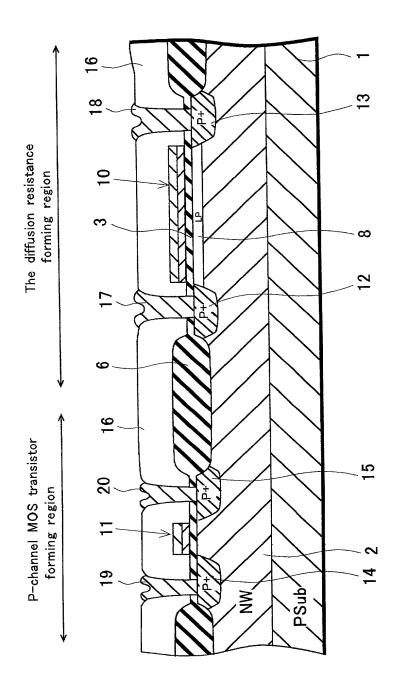


FIG.6



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FIG.7

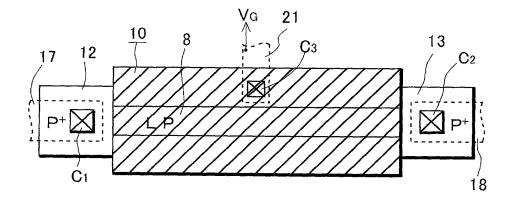
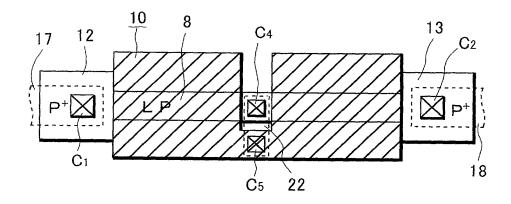


FIG.8



Title: Semiconductor Device and Manufacturing Method Therefor

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FIG.9(A)

R=0

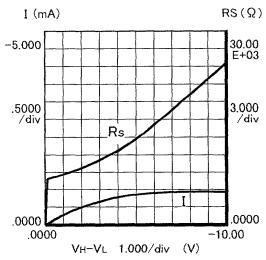


FIG.9(B)

R = 0.2

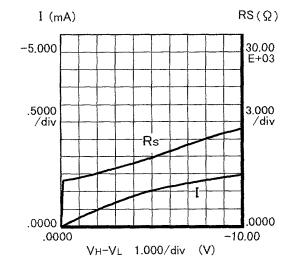
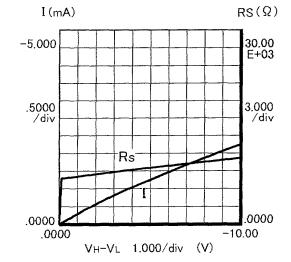


FIG.9(C)

R=0.4

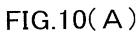


Docket No.: 492322002200

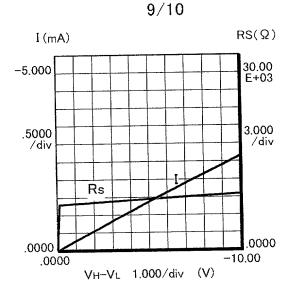
Inventor: Nobuyuki SEKIKAWA et al. Application No.: to be assigned

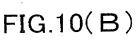
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 $RS(\Omega)$ 

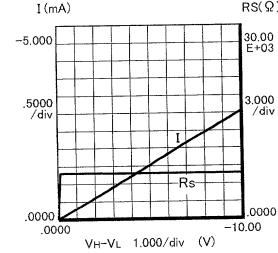


R = 0.5



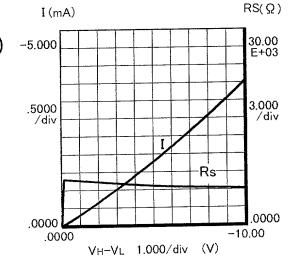


R = 0.6



# FIG.10(C)

R = 0.8

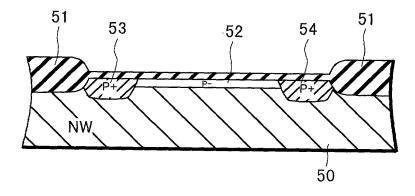


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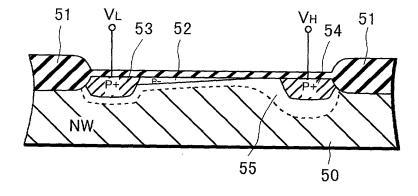
## FIG.11

### PRIOR ART



### FIG.12

#### PRIOR ART



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